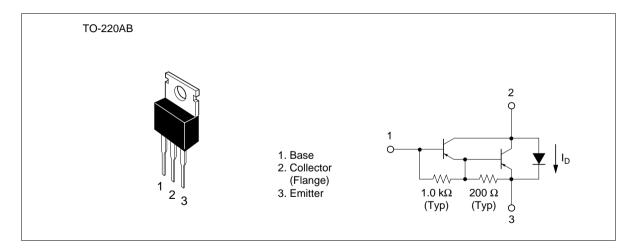
Silicon PNP Triple Diffused

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Application

Power switching complementary pair with 2SD1126(K)

Outline





Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Symbol	Rating	Unit
V _{CBO}	-120	V
V _{CEO}	-120	V
V _{EBO}	-7	V
Ι _c	-10	А
I _{C(peak)}	-15	А
۱ _D *1	10	А
P _c * ²	50	W
Tj	150	°C
Tstg	-55 to +150	°C
	V _{CBO} V _{CEO} V _{EBO} I _C I _C I _{C(peak)} I _D * ¹ P _C * ² Tj	V_{CBO} -120 V_{CEO} -120 V_{CEO} -7 I_c -10 I_{c} -15 I_{D}^{*1} 10 P_c^{*2} 50 Tj 150

Notes: 1. Value at $T_c = 25^{\circ}C$

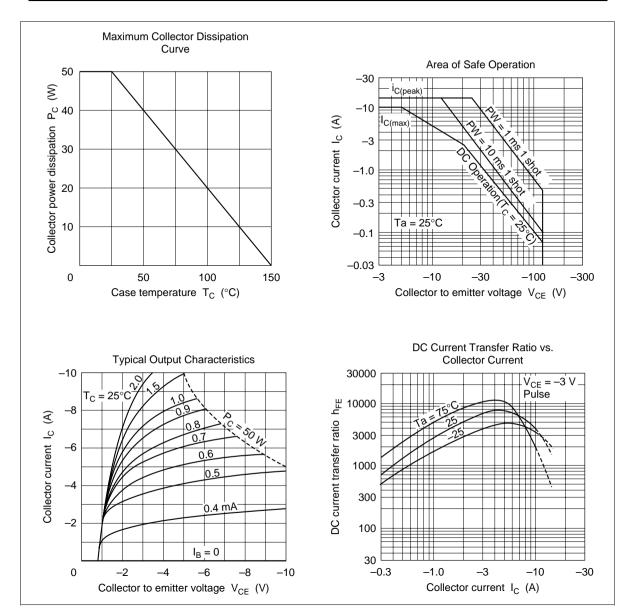
2. $PW \le 1 \text{ ms } 1 \text{ shot}$

Electrical Characteristics ($Ta = 25^{\circ}C$)

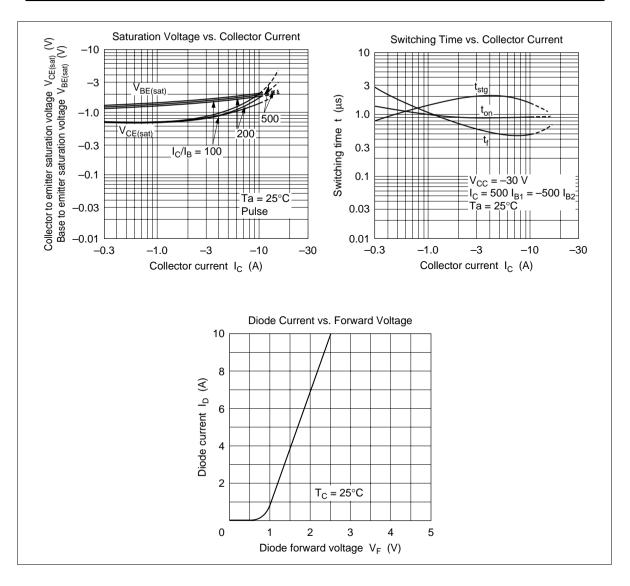
Item	Symbol	Min	Тур	Мах	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-120	_	_	V	$I_c = -25$ mA, $R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-7	_	_	V	$I_{\rm E} = -200$ mA, $I_{\rm C} = 0$
Collector cutoff current	I _{CBO}	_		-100	μΑ	$V_{CB} = -120 \text{ V}, I_E = 0$
	I _{CEO}	—	—	-10	μΑ	$V_{ce} = -100 \text{ V}, \text{ R}_{be} = \infty$
DC current transfer ratio	h _{FE}	1000		20000		$V_{ce} = -3 V, I_c = -5 A^{*1}$
Collector to emitter saturation	$V_{\text{CE(sat)1}}$	_		-1.5	V	$I_{\rm c} = -5$ A, $I_{\rm B} = -10$ mA ^{*1}
	$V_{\text{CE(sat)2}}$	—	—	-3.0	V	$I_{\rm c} = -10$ A, $I_{\rm B} = -0.1$ A ^{*1}
Base to emitter saturation	$V_{BE(sat)1}$	_		-2.0	V	$I_{\rm c} = -5$ A, $I_{\rm B} = -10$ mA ^{*1}
voltage	$V_{BE(sat)^2}$	_		-3.5	V	$I_{\rm c} = -10$ A, $I_{\rm B} = -0.1$ A ^{*1}
C to E diode forward voltage	V _D	—	—	3.0	V	$I_{\rm D} = 10 \ {\rm A}^{*1}$
Turn on time	t _{on}	—	0.8		μs	$V_{cc} = -30 \text{ V}$
Turn off time	t _{off}		4.0		μs	$I_{\rm C} = -5 \text{ A}, I_{\rm B1} = -I_{\rm B2} = -10 \text{ mA}$

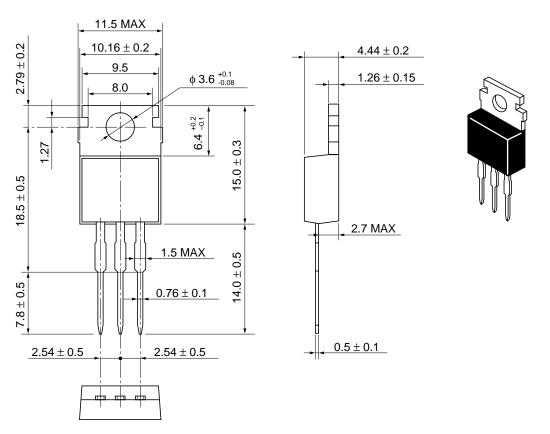
Note: 1. Pulse test

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Hitachi Code	TO-220AB
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	1.8 g

Cautions

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